

# MA2ZD02

## Silicon epitaxial planar type

For high-frequency rectification

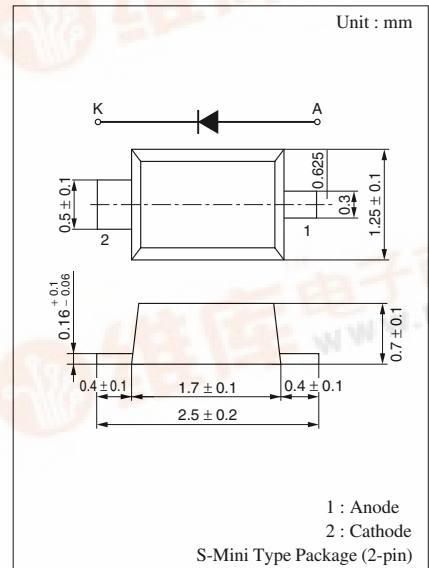
### ■ Features

- Mini package (S-mini type 2-pin)
- Reverse current (DC value)  $V_R$  is low

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

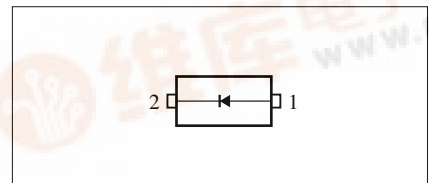
| Parameter                                  | Symbol      | Rating      | Unit             |
|--|-------------|-------------|------------------|
| Reverse voltage (DC)                       | $V_R$       | 20          | V                |
| Repetitive peak reverse voltage            | $V_{RRM}$   | 20          | V                |
| Average forward current                    | $I_{F(AV)}$ | 500         | mA               |
| Non-repetitive peak forward surge current* | $I_{FSM}$   | 3           | A                |
| Junction temperature                       | $T_j$       | 125         | $^\circ\text{C}$ |
| Storage temperature                        | $T_{stg}$   | -55 to +125 | $^\circ\text{C}$ |

Note) \*: The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)



Marking Symbol: 2H

Internal Connection



### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter              | Symbol   | Conditions   | Min | Typ | Max  | Unit          |
|------------------------|----------|--|-----|-----|------|---------------|
| Reverse current (DC)   | $I_{R1}$ | $V_R = 5 \text{ V}$  |     |     | 1    | $\mu\text{A}$ |
|                        | $I_{R2}$ | $V_R = 10 \text{ V}$   |     |     | 10   | $\mu\text{A}$ |
| Forward voltage (DC)   | $V_{F1}$ | $I_F = 10 \text{ mA}$  |     | 0.3 | 0.4  | V             |
|                        | $V_{F2}$ | $I_F = 500 \text{ mA}$   |     | 0.5 | 0.55 | V             |
| Terminal capacitance   | $C_t$    | $V_R = 0 \text{ V}, f = 1 \text{ MHz}$                                     |     | 60  |      | pF            |
| Reverse recovery time* | $t_{rr}$ | $I_F = I_R = 100 \text{ mA}$<br>$I_{tr} = 0.1 \cdot I_R, R_L = 100 \Omega$ |     | 5   |      | ns            |

Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment

2. Rated input/output frequency: 1 000 MHz

3. \*:  $t_{rr}$  measuring instrument

Bias Application Unit N-50BU

